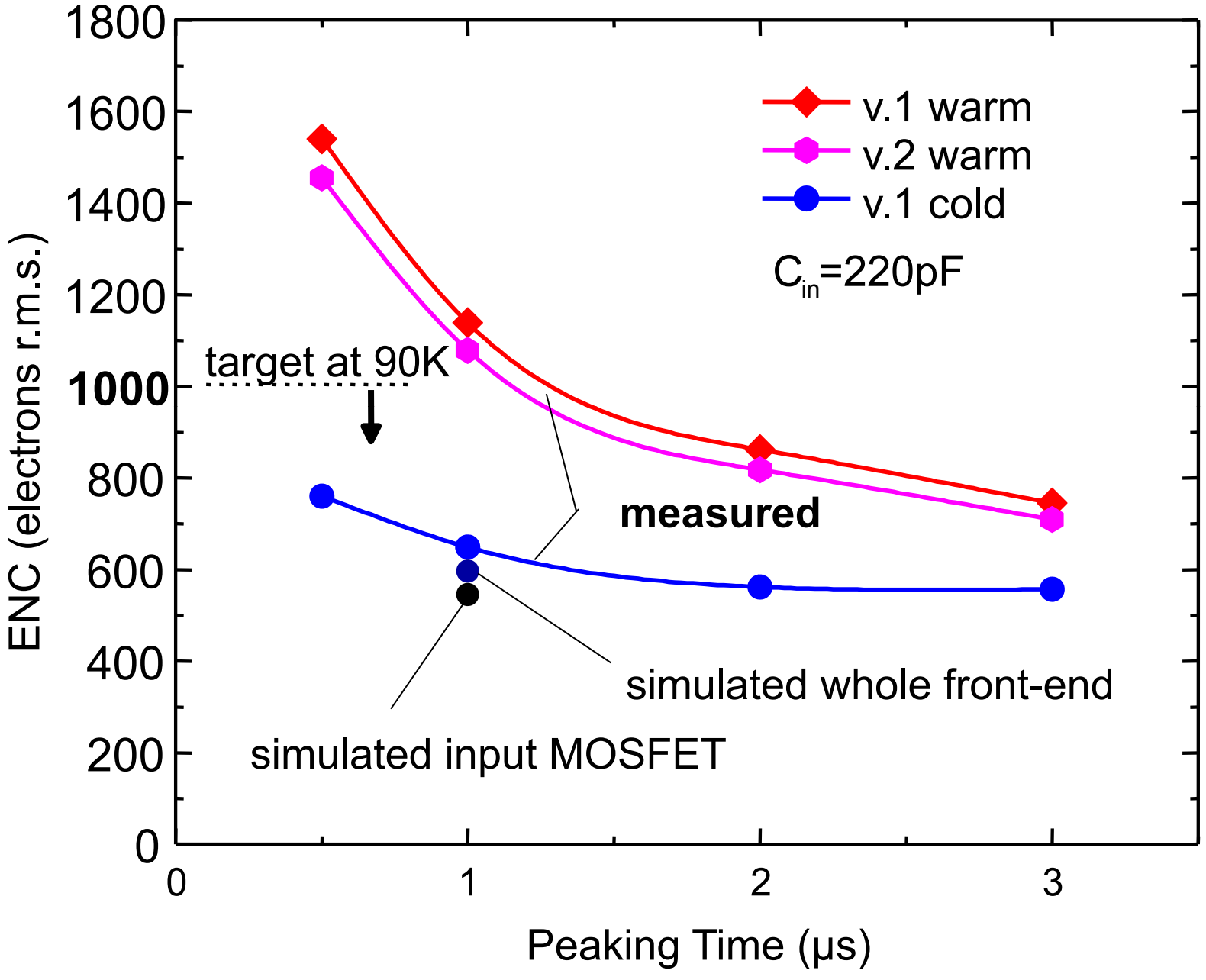
1800
1600
1400
1200
1000
800
600
400
200
0
ENC (electrons r.m.s.)
0
1
2
3
Peaking Time (μs)
v.1 warm
v.2 warm
v.1 cold
C_in=220pF
target at 90K
measured
simulated whole front-end
simulated input MOSFET